100V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$	I_D T_A = +25°C
-100V	350mΩ @ V_{GS}= -10V	-1.6A
	450mΩ @ V_{GS}= -6V	-1.4A

Description

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- DC-DC Converters
- Power Management Functions
- Uninterrupted Power Supply

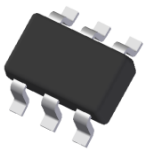
Features and Benefits

- Fast Switching Speed
- Low Gate Drive
- Low Input Capacitance
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

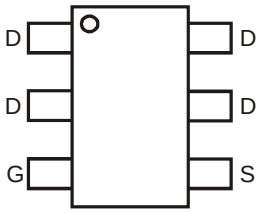
Mechanical Data

- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish - Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.018 grams (Approximate)

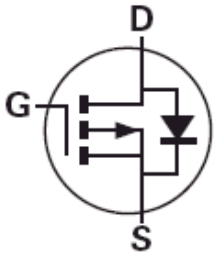
SOT26



Top View



Pin Out
Top View



Equivalent Circuit

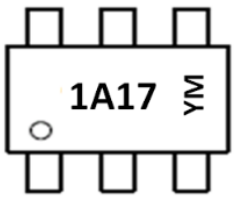
Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
ZXMP10A17E6TA	Standard	SOT26	3,000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

SOT26



1A17 = Product Type Marking Code
YM = Date Code Marking
Y or $\overline{Y}$ = Year (ex: C = 2015)
M or $\overline{M}$ = Month (ex: 9 = September)

Date Code Key

Year	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025	2026
Code	C	D	E	F	G	H	I	J	K	L	M	N

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-100	V
Gate-Source Voltage			V_{GS}	±20	V
Continuous Drain Current	V_{GS} = 10V	(Note 6)	I_D	-1.6	A
		T_A = +70°C (Note 6)		-1.3	
		(Note 5)		-1.3	
Pulsed Drain Current	V_{GS}= 10V	(Note 7)	I_{DM}	-7.7	A
Continuous Source Current (Body Diode)		(Note 6)	I_S	-2.1	A
Pulsed Source Current (Body Diode)		(Note 7)	I_{SM}	-7.7	A

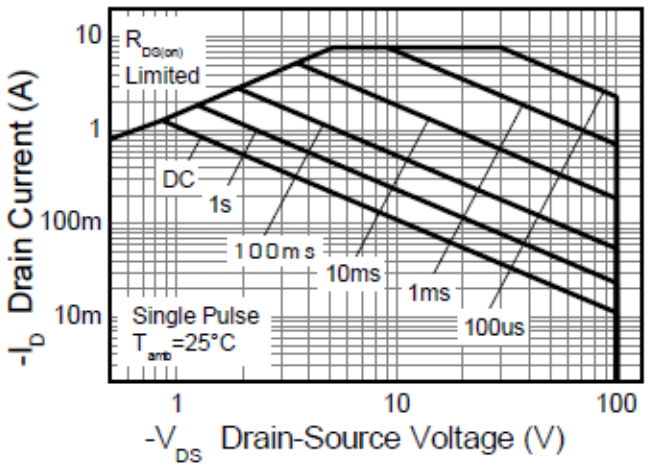
Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 5)	P_D	1.1	W
Linear Derating Factor			8.8	mW/°C
	(Note 6)		1.7	W
			13.7	mW/°C
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	113	°C/W
	(Note 6)		73	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

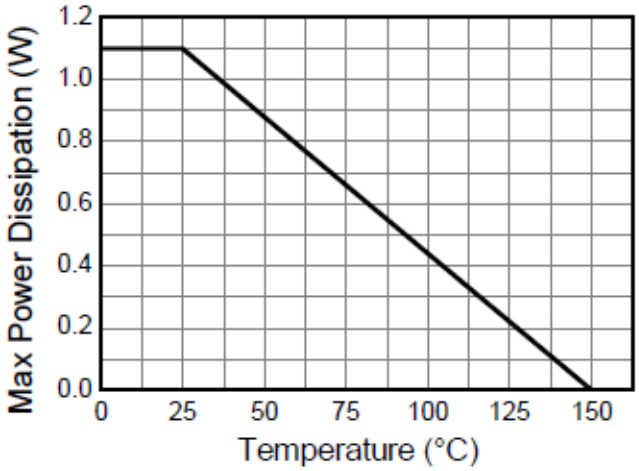
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	-100	—	—	V	I_D = -250µA, V_{GS} = 0V
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-0.5	µA	V_{DS} = -100V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(th)}$	-2	—	-4	V	I_D = -250µA, V_{DS} = V_{GS}
Static Drain-Source On-Resistance (Note 8)	$R_{DS(ON)}$	—	—	0.35	Ω	V_{GS} = -10V, I_D = -1.4A
				0.45		V_{GS} = -6V, I_D = -1.2A
Forward Transconductance (Notes 8 & 9)	g_{fs}	—	2.8	—	S	V_{DS} = -15V, I_D = -1.4A
Diode Forward Voltage (Note 8)	V_{SD}	—	-0.85	-0.95	V	I_S = -1.7A, V_{GS} = 0V
Reverse Recovery Time (Note 9)	t_{rr}		33	—	ns	I_S = -1.5A, di/dt = 100A/µs
Reverse Recovery Charge (Note 9)	Q_{rr}	—	48	—	nC	
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	424	—	pF	V_{DS} = -50V, V_{GS} = 0V F = 1MHz
Output Capacitance	C_{oss}	—	36.6	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	29.8	—	pF	
Total Gate Charge (Note 10)	Q_g	—	7.1	—	nC	V_{GS} = -6V; V_{DS} = -50V, I_D = -1.4A
Total Gate Charge (Note 10)	Q_g	—	10.7	—	nC	V_{GS} = -10V; V_{DS} = -50V, I_D = -1.4A
Gate-Source Charge (Note 10)	Q_{gs}	—	1.7	—	nC	
Gate-Drain Charge (Note 10)	Q_{gd}	—	3.8	—	nC	
Turn-On Delay Time (Note 10)	$t_{D(on)}$	—	3	—	ns	V_{DD} = -50V, V_{GS} = -10V I_D = -1A, $R_G \cong 6\Omega$
Turn-On Rise Time (Note 10)	t_r	—	3.5	—	ns	
Turn-Off Delay Time (Note 10)	$t_{D(off)}$	—	13.4	—	ns	
Turn-Off Fall Time (Note 10)	t_f	—	7.2	—	ns	

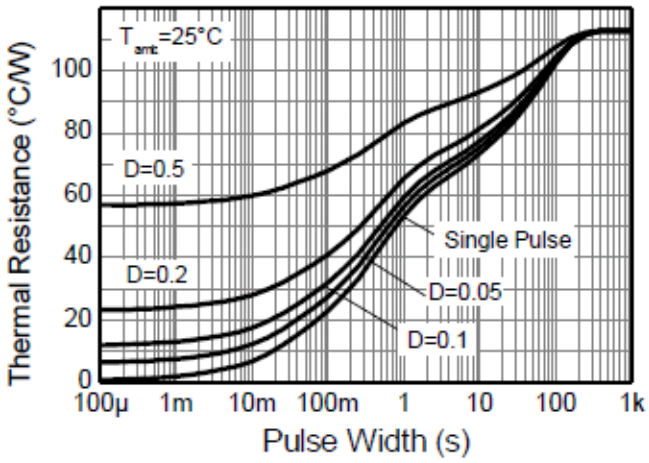
Notes:
5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
6. Same as Note 5, except the device is measured at t ≤ 5 sec.
7. Same as Note 5, except the device is pulsed with D = 0.05 and pulse width 10µs. The pulse current is limited by the maximum junction temperature.
8. Measured under pulsed conditions. Pulse width ≤ 300µs; duty cycle ≤ 2%.
9. For design aid only, not subject to production testing.
10. Switching characteristics are independent of operating junction temperatures.



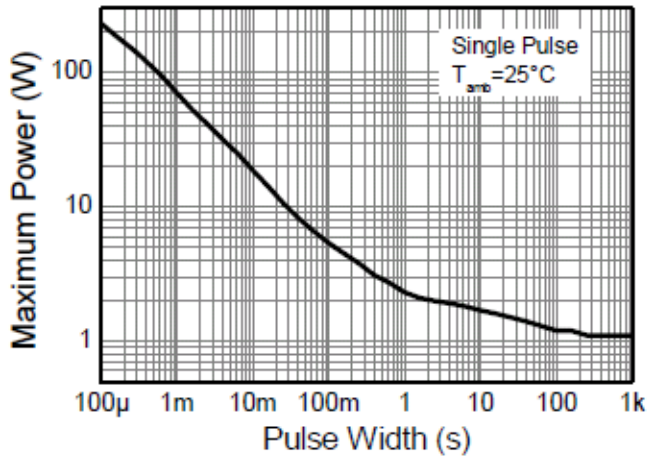
Safe Operating Area



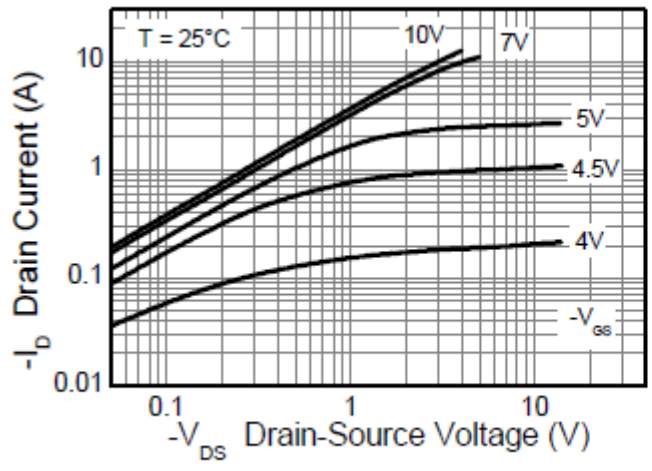
Derating Curve



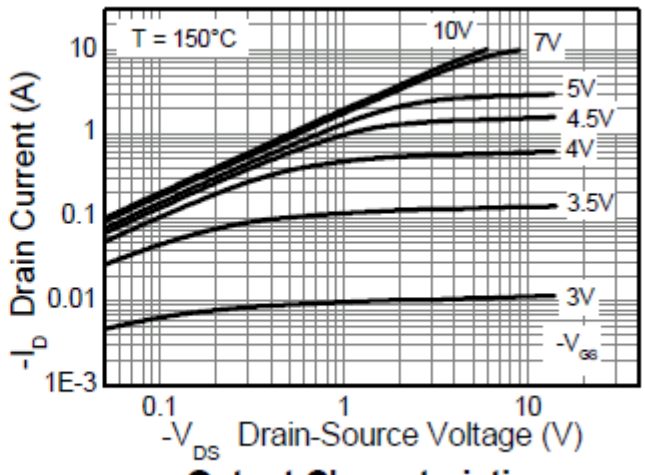
Transient Thermal Impedance



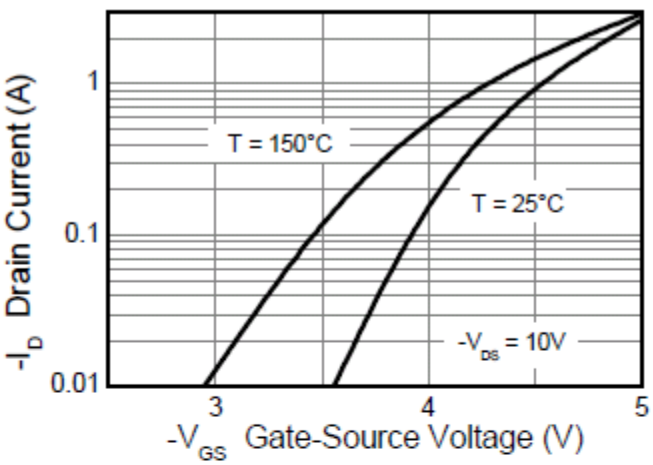
Pulse Power Dissipation



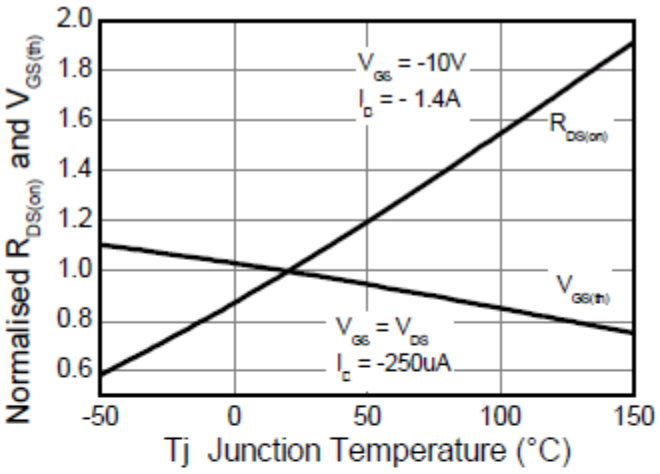
Output Characteristics



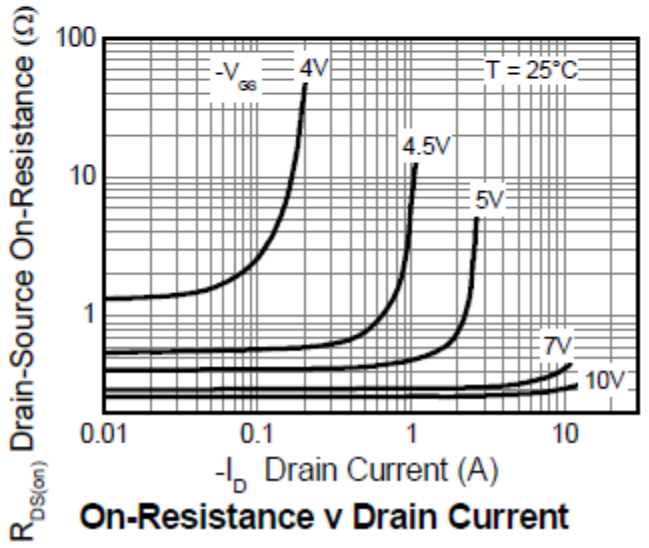
Output Characteristics



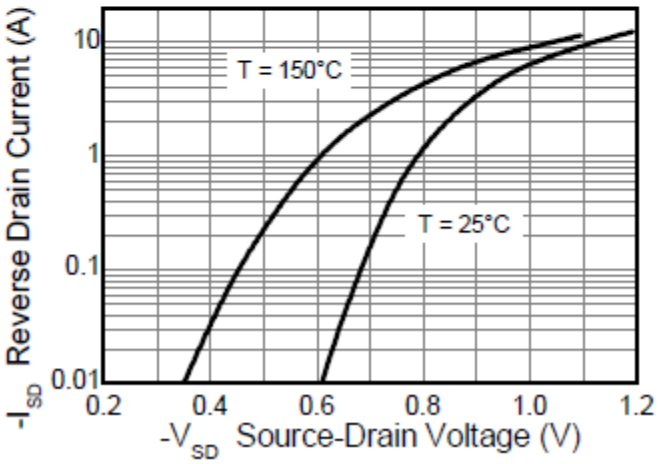
Typical Transfer Characteristics



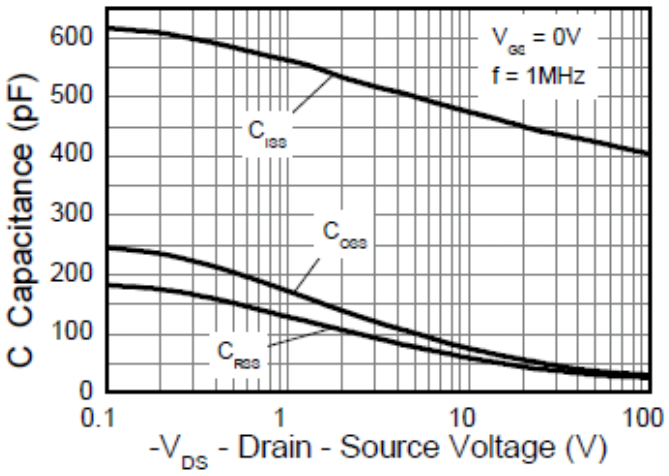
Normalised Curves v Temperature



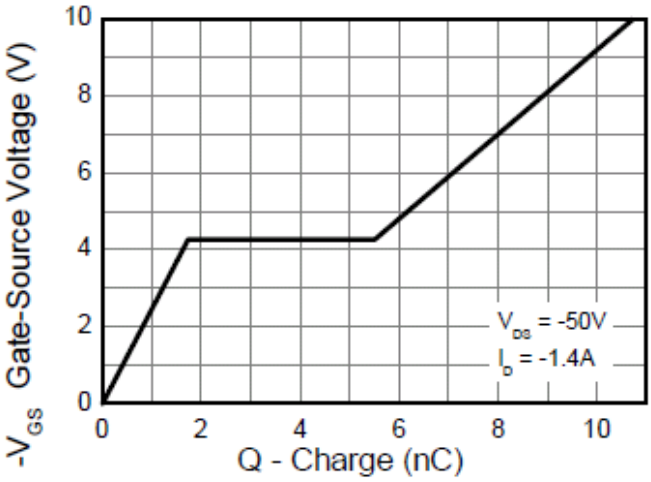
On-Resistance v Drain Current



Source-Drain Diode Forward Voltage

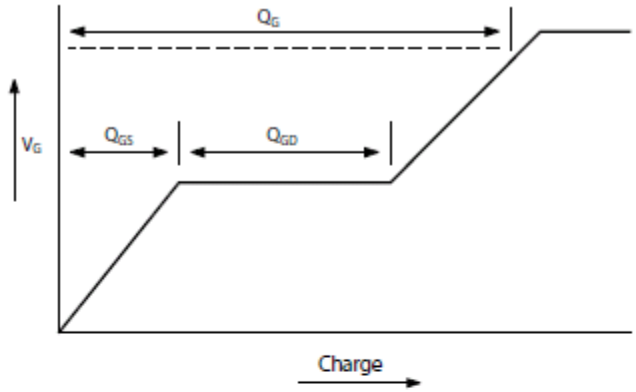


Capacitance v Drain-Source Voltage

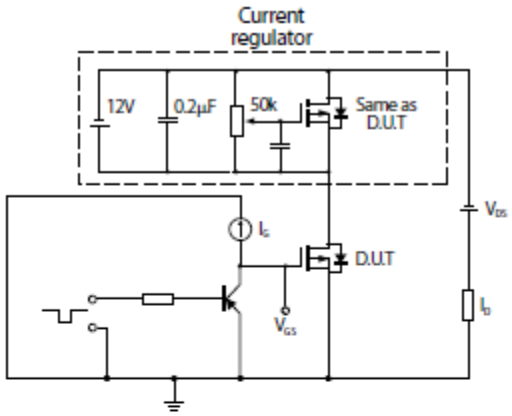


Gate-Source Voltage v Gate Charge

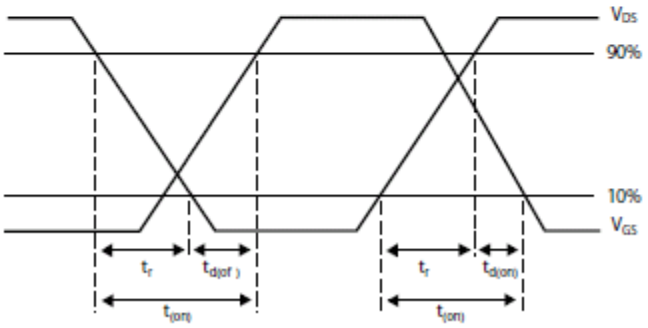
Test Circuits



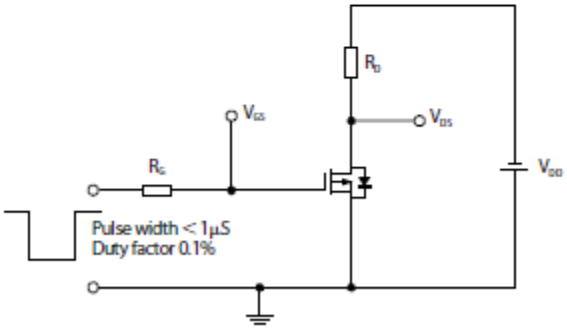
Basic gate charge waveform



Gate charge test circuit



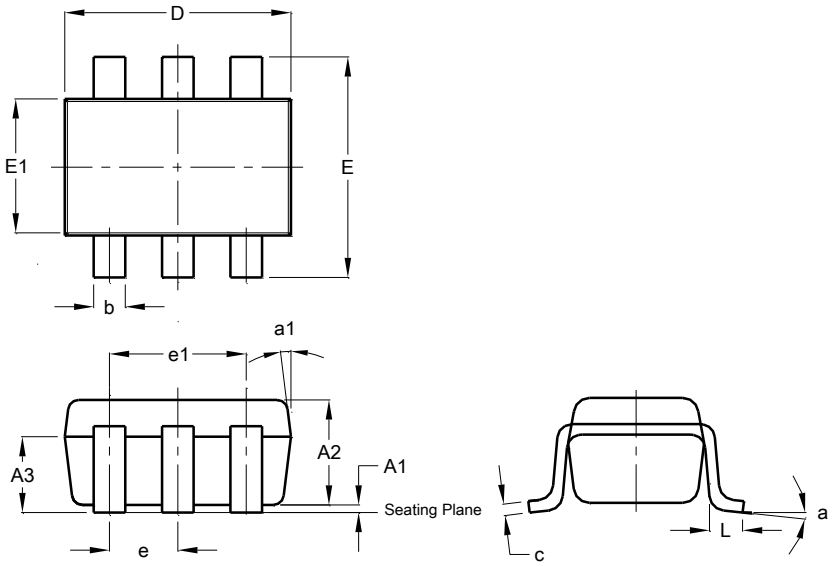
Switching time waveforms



Switching time test circuit

Package Outline Dimensions

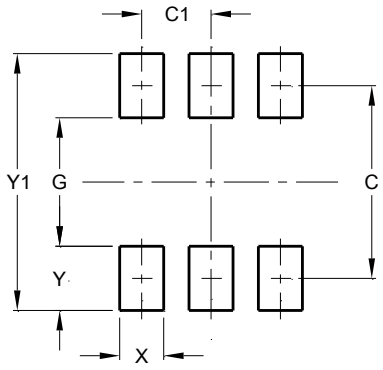
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT26			
Dim	**Min**	**Max**	**Typ**
A1	0.013	0.10	0.05
A2	1.00	1.30	1.10
A3	0.70	0.80	0.75
b	0.35	0.50	0.38
c	0.10	0.20	0.15
D	2.90	3.10	3.00
e	-	-	0.95
e1	-	-	1.90
E	2.70	3.00	2.80
E1	1.50	1.70	1.60
L	0.35	0.55	0.40
a	-	-	8°
a1	-	-	7°
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
C	2.40
C1	0.95
G	1.60
X	0.55
Y	0.80
Y1	3.20

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